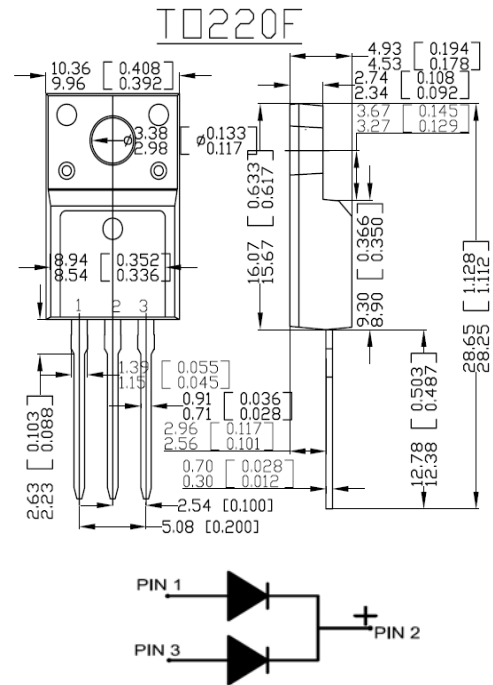


MBRF10200

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss,High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage,High Frequency Inverters,Free Wheeling,and Polarity Protection Applications

Fast Reverse Recovery Time : $t_{rr}=35ns$.



Dimensions in millimeters and (inches)

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Characteristic	Symbol	MBRF10200	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_C	10	A
Maximum Instantaneous Forward Voltage @ $I_F=10A, T_c=25^{\circ}C$ @ $I_F=10A, T_c=125^{\circ}C$ @ $I_F=20A, T_c=25^{\circ}C$ @ $I_F=20A, T_c=125^{\circ}C$	V_F	0.85 0.80 0.95 0.85	V
Peak Reverse Current @ $T_c=25^{\circ}C$ at Rated DC Blocking Voltage @ $T_c=125^{\circ}C$	I_R	10 200	μA
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

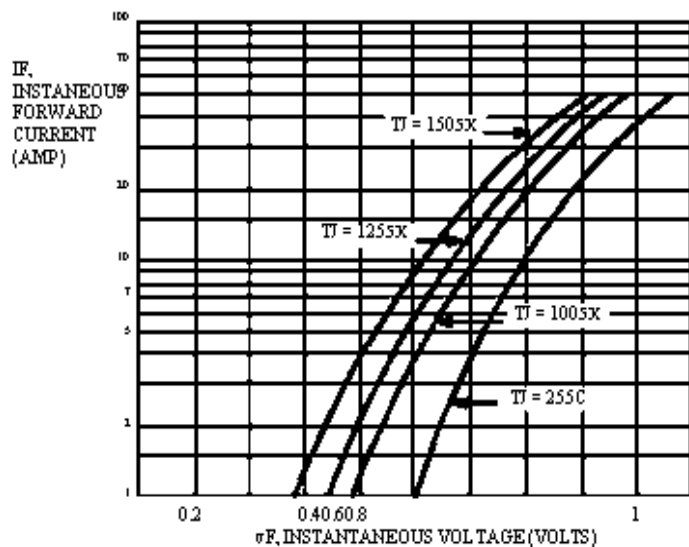


Figure 1. Typical Forward Voltage (Per Leg) vs. Instantaneous Forward Current

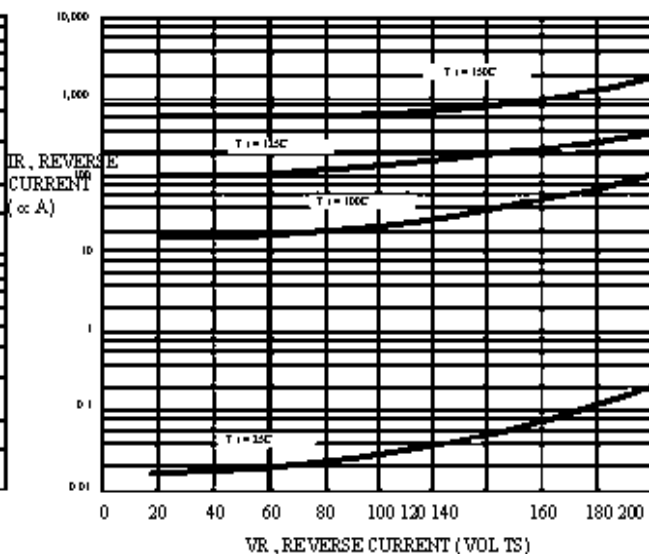


Figure 2. Typical Reverse Current (Per Leg) vs. Reverse Voltage

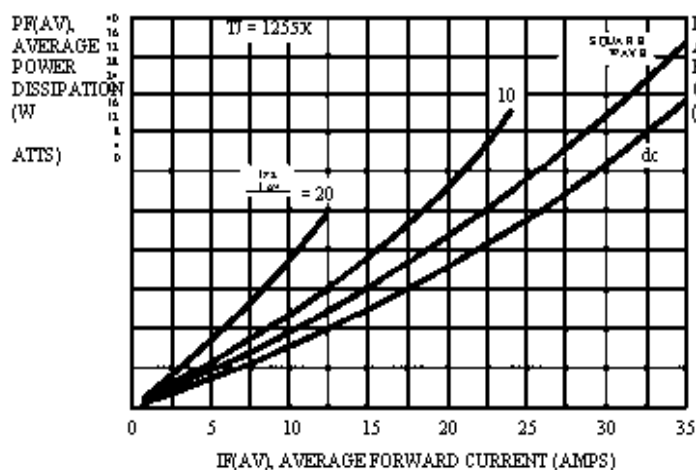


Figure 3. Forward Power Dissipation vs. Average Forward Current

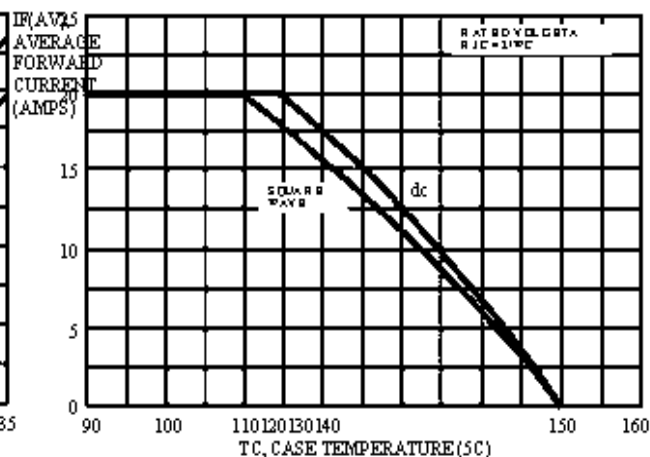


Figure 4. Current Derating vs. Case Temperature

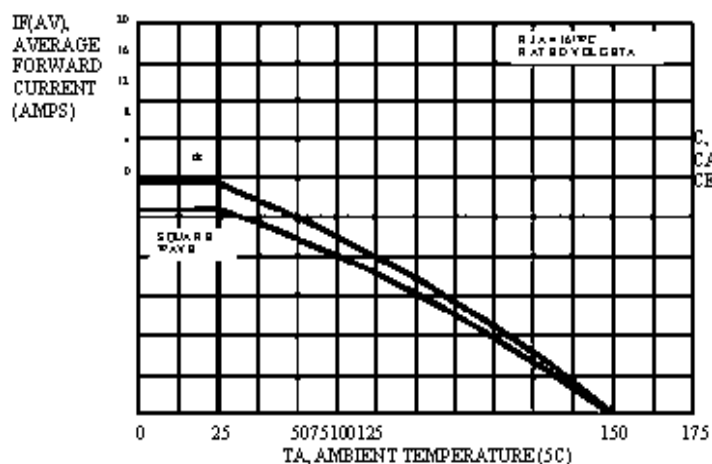


Figure 5. Current Derating vs. Ambient Temperature

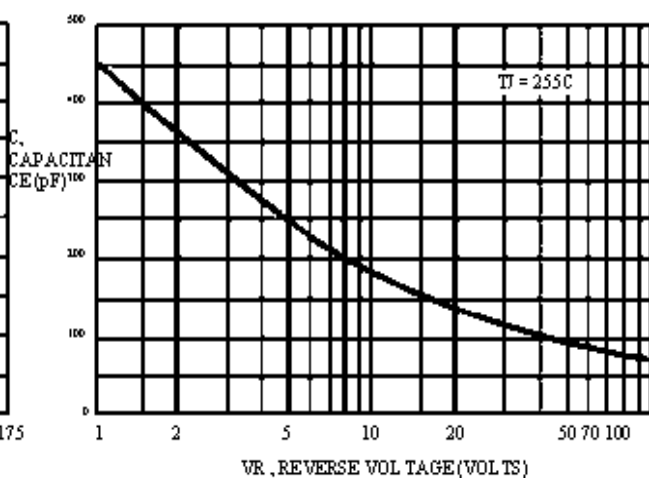


Figure 6. Typical Capacitance (Per Leg) vs. Reverse Voltage